#### TOSHIBA THYRISTOR SILICON PLANAR TYPE

# URSF05G49-1P,URSF05G49-3P,URSF05G49-5P

## LOW POWER SWITCHING AND CONTROL **APPLICATIONS**

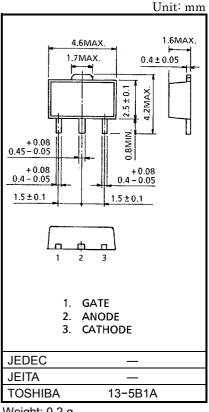
 $\bullet~$  Repetitive Peak Off–State Voltage: VDRM = 400V Repetitive Peak Reverse Voltage : V<sub>RRM</sub> = 400V • Average On-State Current  $: I_{T (AV)} = 500 \text{mA}$ 

• Reduce a Quantity of Parts and Manufacturing

Process Because of Built-in RGK :  $R_{GK} = 1k\Omega$ ,  $2.7k\Omega$ ,  $5.1k\Omega$  (Typ.)

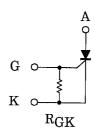
#### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATINGS	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	$V_{ m DRM} \ V_{ m RRM}$	400	V	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive<5ms, $T_j = 0 \sim 125$ °C)	$V_{RSM}$	500	V	
Average On-State Current (Half Sine Waveform)	I <sub>T (AV)</sub>	500	mA	
R.M.S On-State Current	I <sub>T (RMS)</sub>	800	mA	
Peak One Cycle Surge On-State	I <sub>TSM</sub>	9 (50Hz)	Α	
Current (Non-Repetitive)		10 (60Hz)		
I <sup>2</sup> t Limit Value	I <sup>2</sup> t	0.4	A <sup>2</sup> s	
Critical Rate of Rise of On-State Current (Note 1)	di / dt	10	A/µs	
Peak Gate Power Dissipation	$P_{GM}$	0.1	W	
Average Gate Power Dissipation	P <sub>G(AV)</sub>	0.01	W	
Peak Forward Gate Voltage	$V_{FGM}$	3.5	V	
Peak Reverse Gate Voltage	$V_{RGM}$	-5	٧	
Peak Forward Gate Current	I <sub>GM</sub>	125	mA	
Junction Temperature	Tj	-40~125	°C	
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C	



Weight: 0.2 g

#### **EQUIVALENT CIRCUIT**



NOTE 1: di / dt Test condition  $i_G = 5mA$ ,  $t_{gw}=10\mu s$ , t<sub>gr</sub>≤250ns



# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

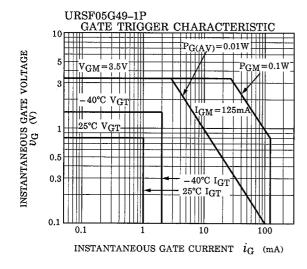
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current		I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub> = Rated	_	_	10	μΑ
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 1A	_	_	1.5	V
Gate Trigger Voltage		V <sub>GT</sub>		_	_	0.8	V
Gate Trigger Current	URSF05G49-1P	l <sub>GT</sub>	$V_D = 6V, R_L = 100\Omega$	250	700	1000	μA
	URSF05G49-3P			100	250	400	
	URSF05G49-5P			50	160	250	
Holding Current	URSF05G49-1P	lн	I <sub>TM</sub> = 500mA, V <sub>D</sub> = 6V	_	_	6	mA
	URSF05G49-3P			_	_	3	
	URSF05G49-5P			_	_	2	
Resistor Between Gate and Cathode	URSF05G49-1P	R <sub>GK</sub>	_	700	1000	1300	Ω
	URSF05G49-3P			1890	2700	3510	
	URSF05G49-5P			3570	5100	6630	
Critical Rate of Rise of Off-State Voltage	URSF05G49-1P	d <sub>V</sub> / dt	V <sub>DRM</sub> = Rated, Exponential Rise	_	200	_	V / µs
	URSF05G49-3P			_	70	_	
	URSF05G49-5P			_	40	_	
Turn-On Time		t <sub>gt</sub>	V <sub>D</sub> = Rated, i <sub>G</sub> = 5mA	_	_	1.5	μs
Thermal Resistance		R <sub>th (j−a)</sub>	Junction to Ambient	_	_	70	°C/W

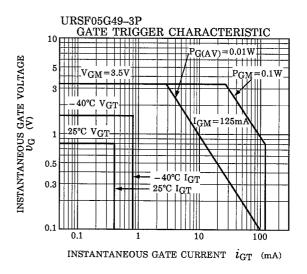
Note: Thermal Resistance Test Condition Use 0.6×30×30mm Alumina Plate

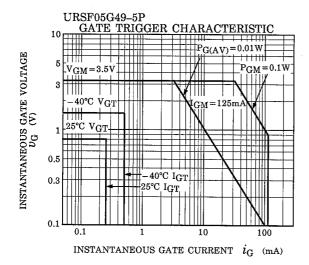
### **MARK**

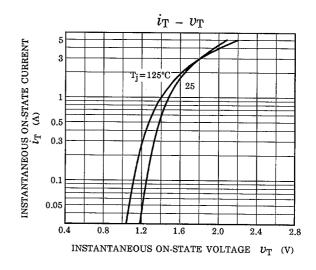


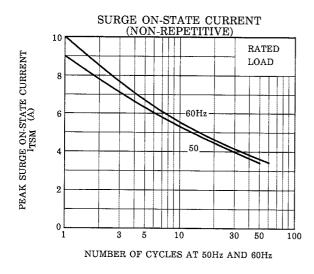
NUMBER	TYPE	MARK		
	URSF05G49-1P	PB		
* 1	URSF05G49-3P	PC		
	URSF05G49-5P	PD		

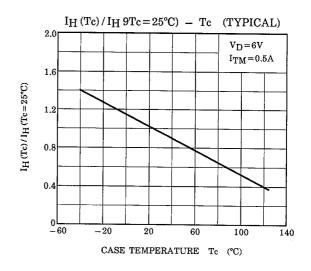


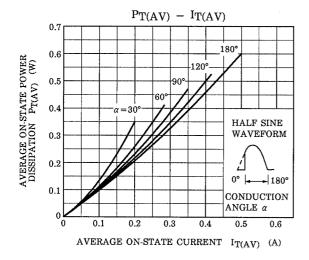


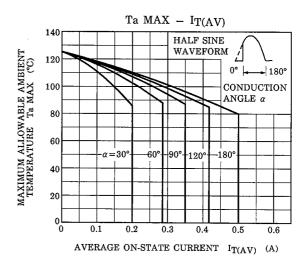


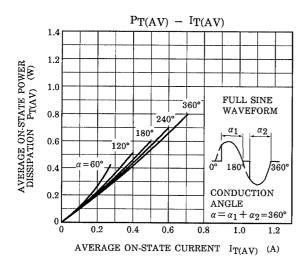


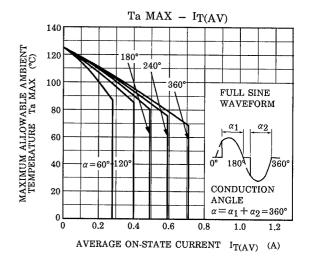


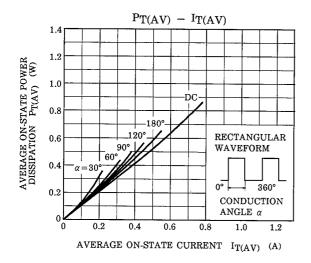


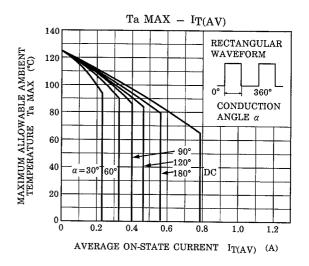


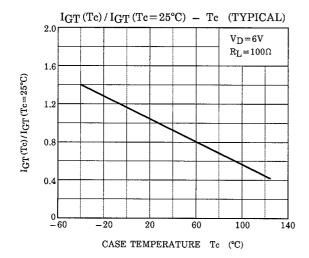


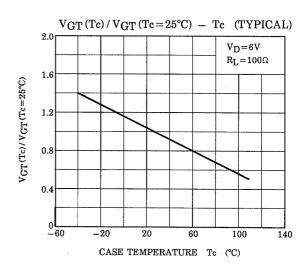


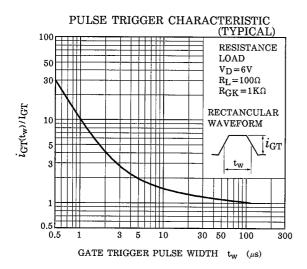


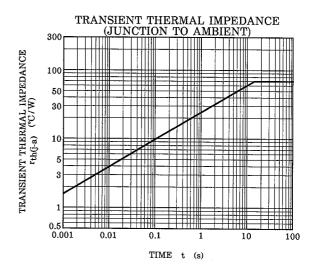












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